



## SEMITRANS® 3

### Fast IGBT4 Modules

SKM200GM12T4

#### Features

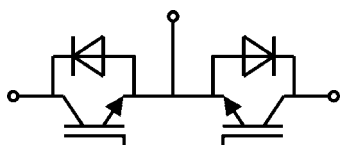
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability, self limiting to  $6 \times I_{Cnom}$
- Fast & soft inverse CAL diodes
- Large clearance (10 mm) and creepage distances (20 mm)
- Isolated copper baseplate using DBC Technology (Direct Copper Bonding)

#### Typical Applications

- Matrix Inverter

#### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max, recomm.  
 $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
<b>IGBT</b>				
$V_{CES}$			1200	V
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	314	A
		$T_c = 80^\circ\text{C}$	242	A
$I_{Cnom}$			200	A
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$		600	A
$V_{GES}$			-20 ... 20	V
$t_{psc}$	$V_{CC} = 800\text{ V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
	$V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$			
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Inverse diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	229	A
		$T_c = 80^\circ\text{C}$	172	A
$I_{Fnom}$			200	A
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$		600	A
$I_{FSM}$	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$		990	A
$T_j$			-40 ... 175	$^\circ\text{C}$
<b>Module</b>				
$I_{t(RMS)}$			500	A
$T_{stg}$			-40 ... 125	$^\circ\text{C}$
$V_{isol}$	AC sinus 50Hz, $t = 1\text{ min}$		4000	V

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
<b>IGBT</b>					
$V_{CE(sat)}$	$I_C = 200\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.8	2.05	V
		$T_j = 150^\circ\text{C}$	2.2	2.4	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	5.0	5.8	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	7.5	8.0	$\text{m}\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 7.6\text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
$C_{ies}$	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	12.3		nF
$C_{oes}$		$f = 1\text{ MHz}$	0.81		nF
$C_{res}$		$f = 1\text{ MHz}$	0.69		nF
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		1130		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$		3.8		$\Omega$
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	185		ns
$t_r$	$I_C = 200\text{ A}$ $V_{GE} = \pm 15\text{ V}$	$T_j = 150^\circ\text{C}$	40		ns
		$T_j = 150^\circ\text{C}$	21		mJ
$E_{on}$	$R_{Gon} = 1\ \Omega$	$T_j = 150^\circ\text{C}$			mJ
$t_{d(off)}$	$R_{Goff} = 1\ \Omega$	$T_j = 150^\circ\text{C}$	425		ns
$t_f$	$di/dt_{on} = 5500\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	82		ns
$E_{off}$	$di/dt_{off} = 2300\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	20		mJ
$R_{th(j-c)}$	per IGBT			0.14	K/W



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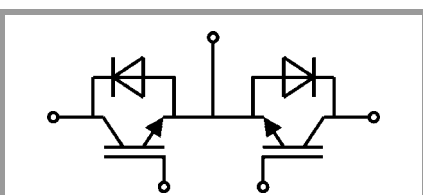
### Typical Applications

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### Remarks

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 $T_{op} = -40 \dots +150^\circ\text{C}$ , product rel. results valid for  $T_j = 150^\circ$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{EC}$	$I_F = 200 \text{ A}$ $V_{GE} = 0 \text{ V}$ chip	$T_j = 25^\circ\text{C}$		2.2	2.52	V
		$T_j = 150^\circ\text{C}$		2.15	2.47	V
$V_{F0}$		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$		4.5	5.1	m $\Omega$
		$T_j = 150^\circ\text{C}$		6.3	6.8	m $\Omega$
$I_{RRM}$	$I_F = 200 \text{ A}$	$T_j = 150^\circ\text{C}$		174		A
$Q_{rr}$	$di/dt_{off} = 4450 \text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		33		$\mu\text{C}$
$E_{rr}$	$V_{GE} = \pm 15 \text{ V}$ $V_{CC} = 600 \text{ V}$	$T_j = 150^\circ\text{C}$		13		mJ
$R_{th(j-c)}$	per diode				0.26	K/W
<b>Module</b>						
$L_{CE}$				15	20	nH
$R_{CC'+EE'}$	terminal-chip	$T_c = 25^\circ\text{C}$		0.25		m $\Omega$
		$T_c = 125^\circ\text{C}$		0.5		m $\Omega$
$R_{th(c-s)}$	per module			0.02	0.038	K/W
$M_s$	to heat sink M6			3	5	Nm
$M_t$		to terminals M6		2.5	5	Nm
						Nm
$w$					325	g



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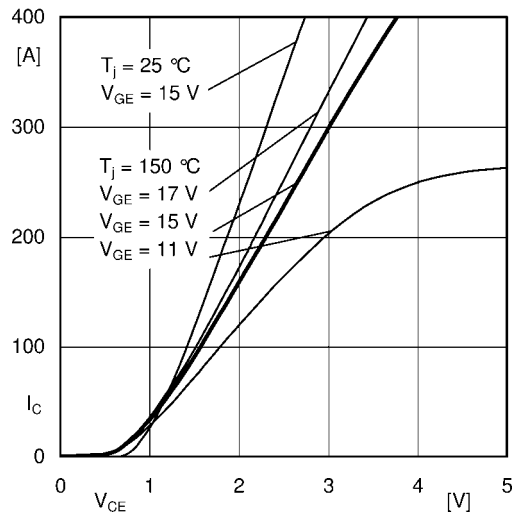


Fig. 1: Typ. output characteristic, inclusive  $R_{CC'+EE'}$

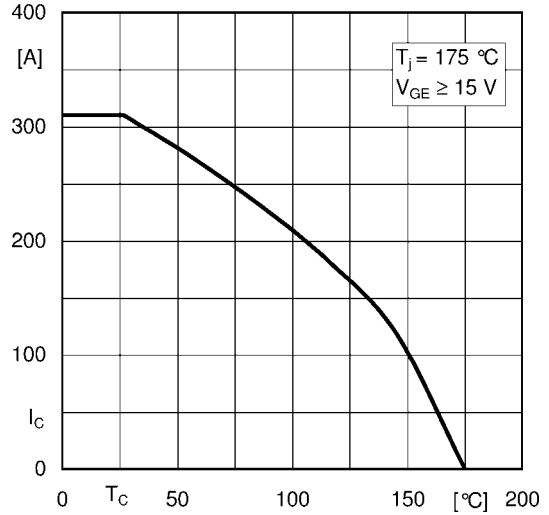


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

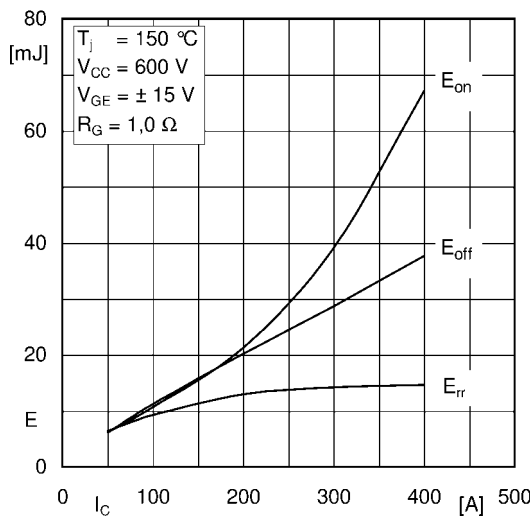


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

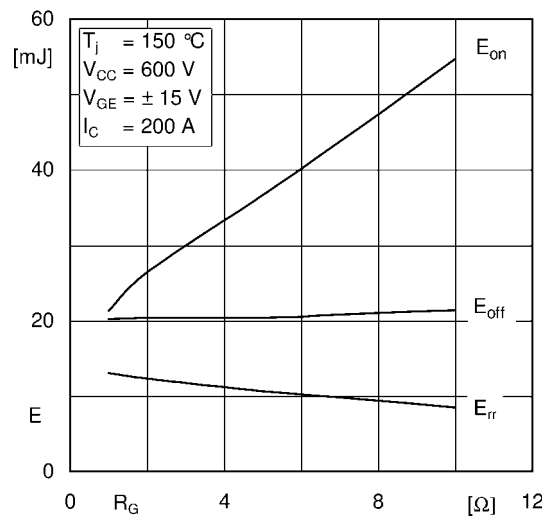


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

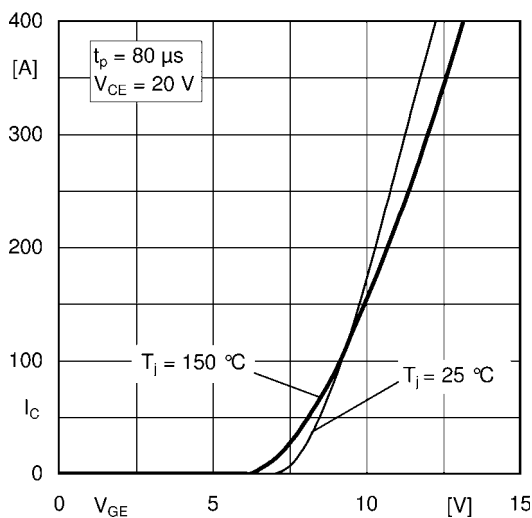


Fig. 5: Typ. transfer characteristic

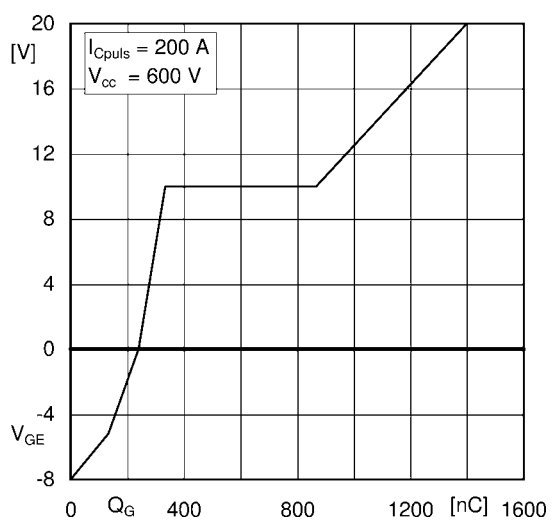
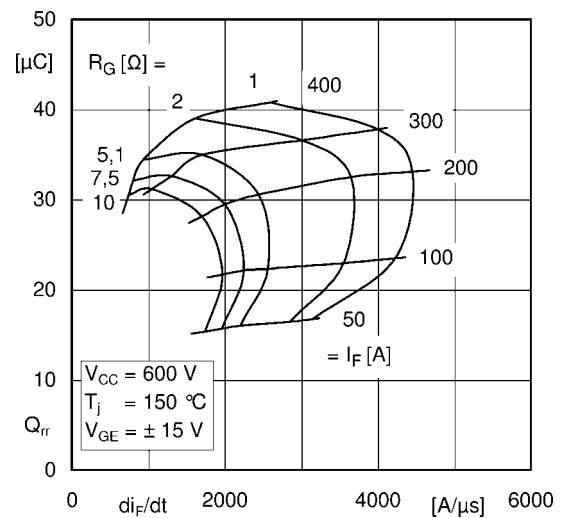
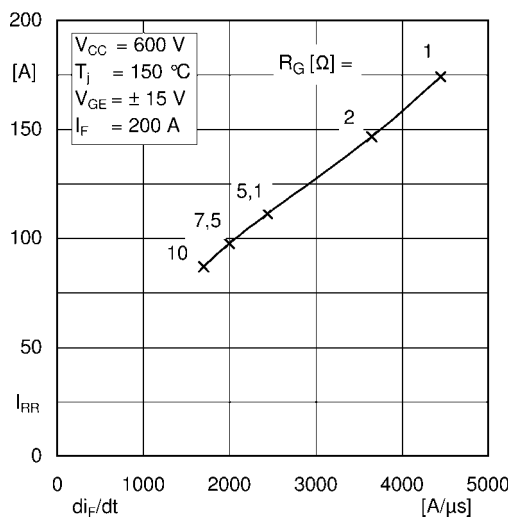
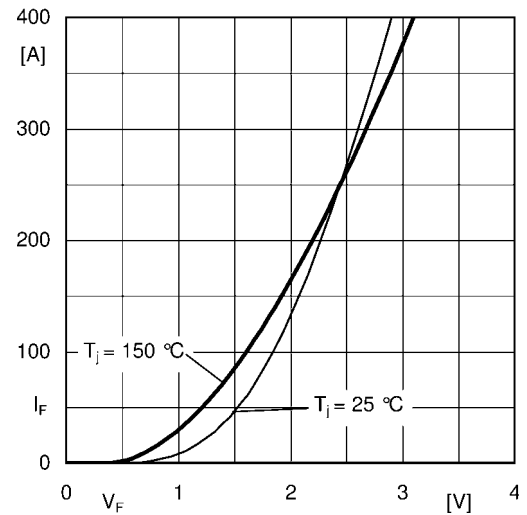
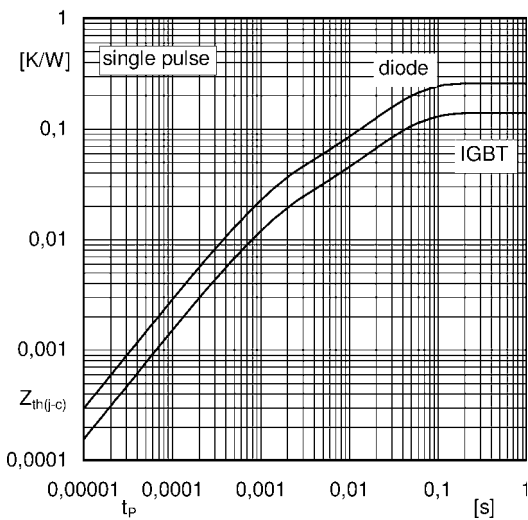
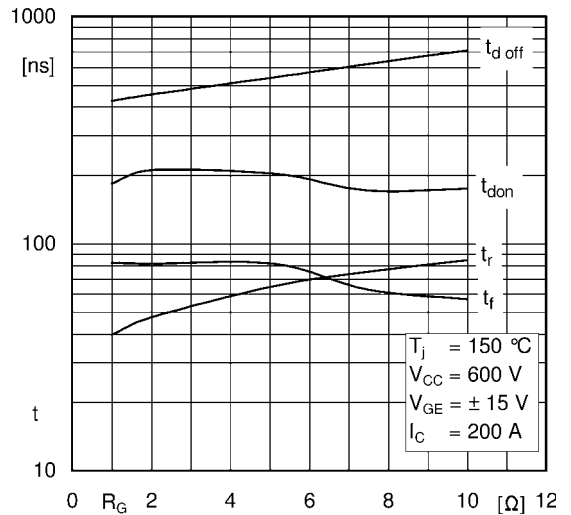
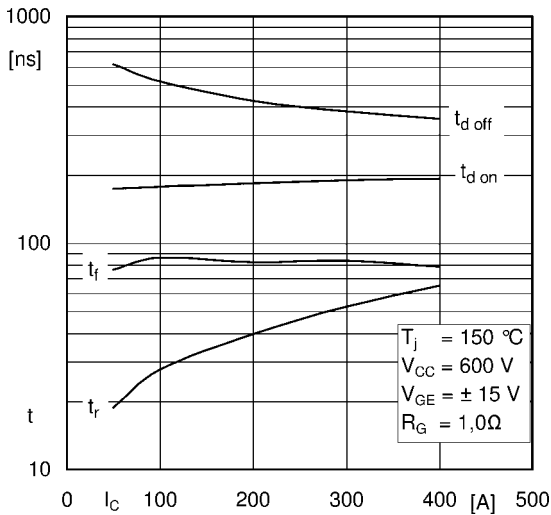
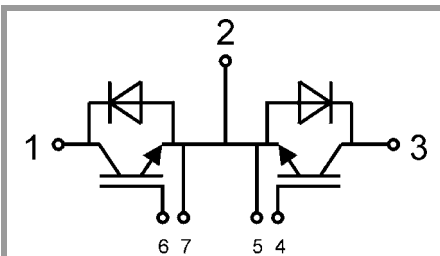


Fig. 6: Typ. gate charge characteristic





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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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